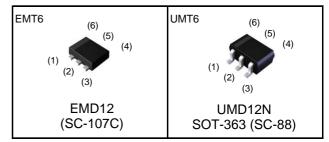
# EMD12 / UMD12N

NPN + PNP Complex Digital Transistors (Bias Resistor Built-in Transistors)

## <For DTr1(NPN)>

Parameter	Value
V <sub>CC</sub>	50V
I <sub>C(MAX.)</sub>	100mA
R <sub>1</sub>	47kΩ
$R_2$	47kΩ

#### Outline



**Datasheet** 

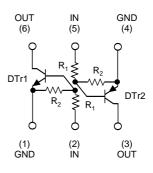
#### <For DTr2(PNP)>

Parameter	Value
V <sub>CC</sub>	-50V
I <sub>C(MAX.)</sub>	-100mA
R <sub>1</sub>	47kΩ
$R_2$	47kΩ

#### Features

- 1) Both the DTC144E chip and DTA144E chip in one package.
- 2) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 3) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making the circuit design easy.
- 5) Lead Free/RoHS Compliant.

## •Inner circuit



#### Application

Inverter circuit, Interface circuit, Driver circuit

#### Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMD12	EMT6	1616	T2R	180	8	8,000	D12
UMD12N	UMT6	2021	TR	180	8	3,000	D12

## ● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	DTr1(NPN)	DTr2(PNP)	Unit
Supply voltage	V <sub>cc</sub>	50	-50	V
Input voltage	V <sub>IN</sub>	-10 to +40	-40 to +10	V
Output current	Io	30	-30	mA
Collector current	I <sub>C(MAX.)</sub> *1	100	-100	mA
Power dissipation	P <sub>D</sub> *2	150 (7	「otal) <sup>*3</sup>	mW
Junction temperature	T <sub>j</sub>	T <sub>j</sub> 150		°C
Range of storage temperature	T <sub>stg</sub>	−55 to +150		°C

## ●Electrical characteristics(Ta = 25°C) <For DTr1(NPN)>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input voltage	$V_{I(off)}$	$V_{CC} = 5V, I_{O} = 100 \mu A$	ı	1	0.5	V
input voitage	$V_{I(on)}$	$V_0 = 0.3V, I_0 = 2mA$	3.0	-	1	V
Output voltage	$V_{O(on)}$	$I_{O}/I_{I} = 10 \text{mA} / 0.5 \text{mA}$	-	0.1	0.3	V
Input current	I <sub>I</sub>	V <sub>I</sub> = 5V	-	-	0.18	mA
Output current	I <sub>O(off)</sub>	$V_{CC} = 50V, V_I = 0V$	ı	-	0.5	μΑ
DC current gain	Gı	$V_O = 5V$ , $I_O = 5mA$	68	-	-	-
Input resistance	R <sub>1</sub>	-	32.9	47	61.1	kΩ
Resistance ratio	R <sub>2</sub> /R <sub>1</sub>	-	0.8	1	1.2	-
Transition frequency	f <sub>T</sub> *1	$V_{CE} = 10V, I_{E} = -5mA$ f = 100MHz		250		MHz

## •Electrical characteristics(Ta = 25°C) <For DTr2(PNP)>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input voltage	$V_{I(off)}$	$V_{CC} = -5V, I_{O} = -100 \mu A$	-	-	-0.5	V
input voitage	$V_{I(on)}$	$V_0 = -0.3V$ , $I_0 = -2mA$	-3.0	-	-	V
Output voltage	$V_{O(on)}$	$I_0/I_1 = -10 \text{mA} / -0.5 \text{mA}$	-	-0.1	-0.3	V
Input current	I <sub>I</sub>	$V_1 = -5V$	-	-	-0.18	mA
Output current	I <sub>O(off)</sub>	$V_{CC} = -50V, V_I = 0V$	-	-	-0.5	μΑ
DC current gain	G <sub>I</sub>	$V_0 = -5V, I_0 = -5mA$	68	-	-	-
Input resistance	R <sub>1</sub>	-	32.9	47	61.1	kΩ
Resistance ratio	R <sub>2</sub> /R <sub>1</sub>	-	0.8	1	1.2	-
Transition frequency	f <sub>T</sub> *1	$V_{CE} = -10V, I_{E} = 5mA$ f = 100MHz	-	250	-	MHz

<sup>\*1</sup> Characteristics of built-in transistor

<sup>\*2</sup> Each terminal mounted on a reference footprint

<sup>\*3 120</sup>mW per element must not be exceeded.

#### ●Electrical characteristic curves (Ta = 25°C) <For DTr1(NPN)>

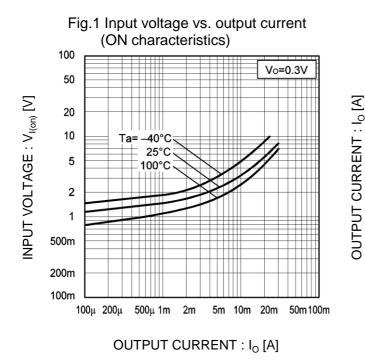


Fig.2 Output current vs. input voltage (OFF characteristics) 10m Vcc=5V 5m Ta=100°C 2m 25°C 1m 40°C 500μ 200μ 100μ 50μ 20μ 10μ 5μ 2μ 1μ 0 0.5 1.0 1.5 2.0 2.5 3.0 INPUT VOLTAGE :  $V_{I(off)}[V]$ 

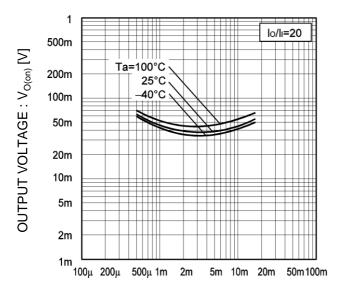
Fig.3 Output current vs. output voltage  $I_{i}=$ 30 Ta=25°C 120μΑ 110μΑ OUTPUT CURRENT : Io [mA] 100μΑ 90μΑ 20 80μΑ 70μΑ 60μΑ 10 50μΑ 40μΑ 30μΑ 0 5 0 10 OUTPUT VOLTAGE: Vo [V]

1k V<sub>O</sub>= 5V 500 Ta= 100°C CURRENT GAIN: G 200 25°C 40°C 100 50 20 10 5 2 100μ 200μ 500μ 1m 2m 5m 10m 20m 50m 100m OUTPUT CURRENT: Io [A]

Fig.4 DC current gain vs. output current

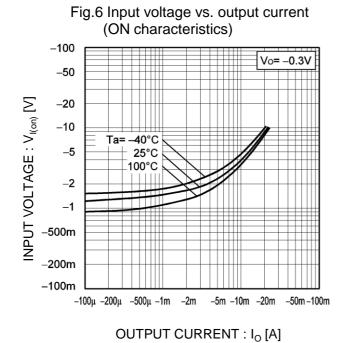
#### ●Electrical characteristic curves (Ta = 25°C) <For DTr1(NPN)>

Fig.5 Output voltage vs. output current



#### OUTPUT CURRENT : Io [A]

#### ●Electrical characteristic curves (Ta = 25°C) <For DTr2(PNP)>



(OFF characteristics) -10m Vcc= -5V -5m –2m Ta=100°C OUTPUT CURRENT : Io [A] 25°C –1m 40°C –500μ  $-200 \mu$ -100μ -50<sub>µ</sub> **–20**μ –10µ -5μ –2µ -1μ -0.5-1.0-1.5-2.0 -2.5 -3.0INPUT VOLTAGE :  $V_{I(off)}[V]$ 

Fig.7 Output current vs. input voltage

## ●Electrical characteristic curves (Ta = 25°C) <For DTr2(PNP)>

Fig.8 Output current vs. output voltage

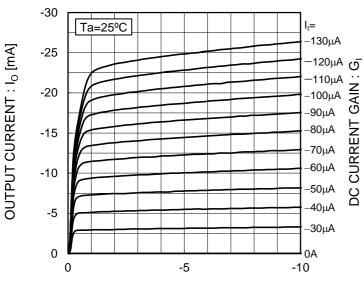
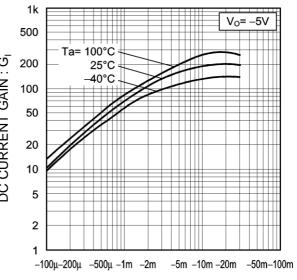


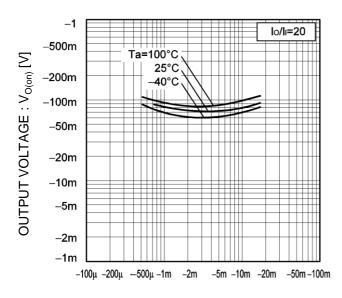
Fig.9 DC current gain vs. output current



OUTPUT CURRENT: Io [A]

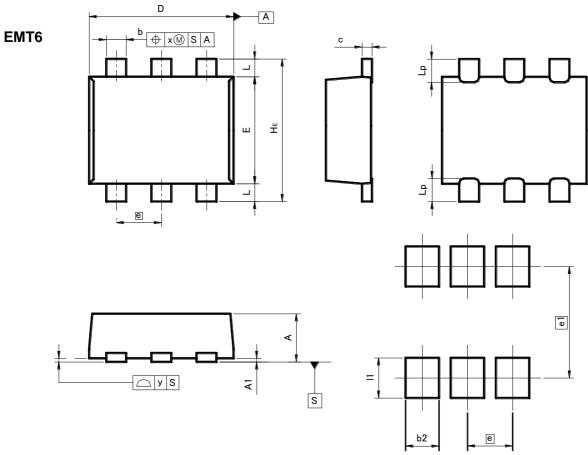
Fig.10 Output voltage vs. output current

OUTPUT VOLTAGE: Vo [V]



OUTPUT CURRENT: Io [A]

## ●Dimensions (Unit : mm)



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

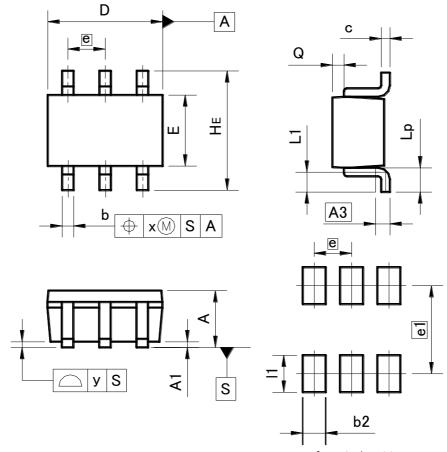
DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	0.45	0.55	0.018	0.022	
A1	0.00	0.10	0.000	0.004	
b	0.17	0.27	0.007	0.011	
С	0.08	0.18	0.003	0.007	
D	1.50	1.70	0.059	0.067	
Е	1.10	1.30	0.043	0.051	
е	0.	50	0.020		
HE	1.50	1.70	0.059	0.067	
L	0.10	0.30	0.004	0.012	
Lp	_	0.35		0.014	
х	_	0.10	_	0.004	
у	_	0.10	_	0.004	

DIM	MILIMETERS		INCHES		
DIM		MIN	MAX	MIN	MAX
	b2	_	0.37	_	0.015
Ī	e1	1.25		0.0	49
	l1	ı	0.45	ı	0.018

Dimension in mm / inches

## ●Dimensions (Unit:mm)





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INCHES		
DIIVI	MIN	MAX	MIN	MAX	
Α	0.80	1.00	0.031	0.039	
A1	0.00	0.10	0.000	0.004	
A3	0.3	25	0.0	10	
b	0.15	0.30	0.006	0.012	
С	0.10	0.20	0.004	0.008	
D	1.90	2.10	0.075	0.083	
E	1.15	1.35	0.045	0.053	
е	0.0	0.65		26	
HE	2.00	2.20	0.079	0.087	
L1	0.20	0.50	0.008	0.020	
Lp	0.25	0.55	0.010	0.022	
Q	0.10	0.30	0.004	0.012	
Х	_	0.10		0.004	
У	_	0.10		0.004	

DIM	MILIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
b2	_	0.40	-	0.016	
e1	1.	55	0.0	061	
l1	_	0.65	_	0.026	

Dimension in mm / inches

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